



GT450HF120T2NH

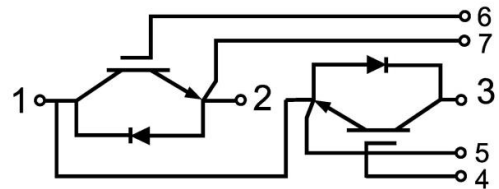
IGBT Module

Preliminary Datasheet

Features:

- Field Stop Trench Gate IGBT
- Short Circuit Rated $>10\mu\text{s}$
- Low Saturation Voltage
- Low Switching Loss
- 100% RBSOA Tested($2\times I_c$)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement

Circuit Diagram



Applications:

- High Power Converters
- Motor Drives
- UPS Systems
- Wind Turbines

IGBT, Inverter

Maximum Rated Values ($T_C=25^\circ\text{C}$ unless otherwise specified)

V_{CES}	Collector-Emitter Blocking Voltage		1200	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Continuous Collector Current	$T_C=80^\circ\text{C}$	450	A
		$T_C=25^\circ\text{C}$	540	A
I_{CM}	Peak Collector Current Repetitive	$t_p=1\text{ms}$	900	A
P_D	Maximum Power Dissipation (IGBT)	$T_C=25^\circ\text{C}$ $T_{Jmax}=150^\circ\text{C}$	2404	W



Electrical Characteristics of IGBT ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Static Characteristics

Symbol	Description	Conditions	Min.	Typ.	Max.	Units
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=17\text{mA}$, $V_{CE}=V_{GE}$	5.0		6.5	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=450\text{A}$, $V_{GE}=15\text{V}$	$T_J=25^{\circ}\text{C}$	2.23		V
			$T_J=125^{\circ}\text{C}$	2.93		V
			$T_J=150^{\circ}\text{C}$	3.19		V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE}=0\text{V}$, $V_{CE}=V_{CES}$, $T_J=25^{\circ}\text{C}$			1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=20\text{V}$, $V_{CE}=0\text{V}$, $T_J=25^{\circ}\text{C}$			400	nA
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}$, $V_{GE}=0\text{V}$, $f=100\text{kHz}$		51.34		nF
C_{oes}	Output Capacitance			2.58		nF
C_{res}	Reveres Transfer Capacitance			0.52		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC}=600V, I_c=450A,$ $R_{Gon}=1\Omega, V_{GE}=\pm 15V,$ Inductive Load	$T_J=25^{\circ}C$		174		ns
			$T_J=125^{\circ}C$		188		
			$T_J=150^{\circ}C$		198		
t_r	Rise Time		$T_J=25^{\circ}C$		45		ns
			$T_J=125^{\circ}C$		53		
			$T_J=150^{\circ}C$		56		
$t_{d(off)}$	Turn-off Delay Time	$V_{CC}=600V, I_c=450A,$ $R_{Goff}=1\Omega, V_{GE}=\pm 15V,$ Inductive Load	$T_J=25^{\circ}C$		217		ns
			$T_J=125^{\circ}C$		244		
			$T_J=150^{\circ}C$		258		
t_f	Fall Time		$T_J=25^{\circ}C$		55		ns
			$T_J=125^{\circ}C$		82		
			$T_J=150^{\circ}C$		84		
E_{on}	Turn-on Switching Loss	$V_{CC}=600V, I_c=450A,$ $R_{Gon}=1\Omega, V_{GE}=\pm 15V,$ $di/dt=6429A/\mu s(T_J=150^{\circ}C),$ Inductive Load	$T_J=25^{\circ}C$		26.6		mJ
			$T_J=125^{\circ}C$		41.6		
			$T_J=150^{\circ}C$		51.8		



E _{off}	Turn-off Switching Loss	V _{CC} =600V, I _C =450A, R _{Goff} =1Ω, V _{GE} =±15V, du/dt=7500V/μs(T _J =150°C), Inductive Load	T _J =25°C		18.7		mJ
			T _J =125°C		24.3		
			T _J =150°C		26.0		
Q _g	Total Gate Charge	V _{GE} =+15V...-15V	T _J =25°C		2897		nC
R _{G(int)}	Internal Gate Resistor				1.0		Ω
I _{SC}	V _{CC} =600V, V _{GE} =+/-15V, T _J =175°C			10			μs
R _{θJC}	Thermal Resistance: Junction-to-Case (per IGBT)					0.052	°C/W

Diode, Inverter

Maximum Rated Values of Diode (T_C=25°C unless otherwise specified)

V _{RRM}	Repetitive Peak Reverse Voltage	T _J =25°C	1200	V
I _F	Diode Continuous Forward Current		450	A
I _{FP}	Peak FWD Current Repetitive	t _p =1ms	900	A

Electrical Characteristics of Diode (T_C=25°C unless otherwise specified)

Symbol	Description	Conditions		Min.	Typ.	Max.	Units
V _F	Forward Voltage	I _F =450A	T _J =25℃		1.85		V
			T _J =125℃		1.96		
			T _J =150℃		1.94		
t _{rr}	Reverse Recovery Time	I _F =450A, -diF/dt=7700A/μs(T _J =150℃), V _R =600V, V _{GE} =-15V	T _J =25℃		267		ns
			T _J =125℃		386		
			T _J =150℃		483		
I _{rr}	Peak Reverse Recovery Current		T _J =25℃		432		A
			T _J =125℃		400		
			T _J =150℃		400		
Q _{rr}	Reverse Recovery Charge		T _J =25℃		43		μC
			T _J =125℃		63		
			T _J =150℃		80		



E _{rec}	Reverse Recovery Energy	I _F =450A, -diF/dt=7700A/μs(T _J =150℃), V _R =600V, V _{GE} =-15V	T _J =25℃		17		mJ
			T _J =125℃		25		
			T _J =150℃		32		
R _{θJC}	Thermal Resistance: Junction-to-Case (per Diode)					0.109	℃/W

Module

Symbol	Description	Conditions	Min.	Typ.	Max.	Units
V _{iso}	Isolation Voltage (All Terminals Shorted)	RMS, f=50Hz, 1minute	2500			V
T _J	Maximum Junction Temperature				150	℃
T _{JOP}	Maximum Operating Junction Temperature Range		-40		+125	℃
T _{stg}	Storage Temperature		-40		+125	℃
CTI	Comparative Tracking Index		200			
R _{θCS}	Case-to-Sink Thermally (Conductive Grease Applied)				0.03	℃/W
T	Power Terminals Screw:M6		3.0		5.0	N·m
T	Mounting Screw:M6		4.0		6.0	N·m
G	Weight			300		g

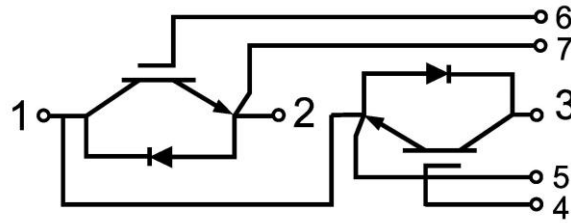
Ordering Information Table

Device code	G	T	450	HF	120	T2N	H
	①	②	③	④	⑤	⑥	⑦

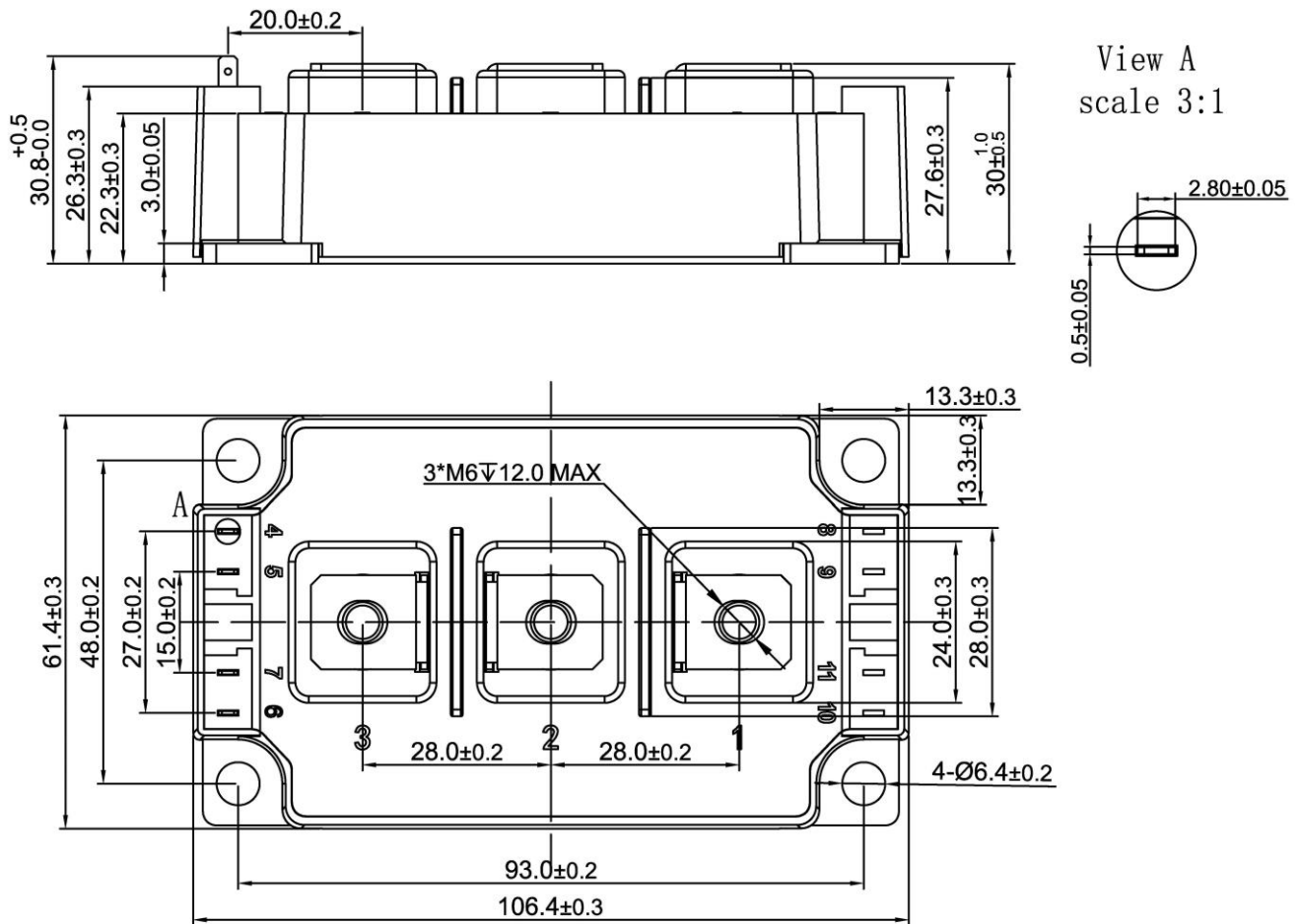
- ① - IGBT Module
- ② - Trench, Low Switching Losses IGBT
- ③ - Rated Current (450=450A)
- ④ - Circuit Configuration: HF (Half Bridge)
- ⑤ - Rated Voltage (120=1200V)
- ⑥ - Package Type
- ⑦ - Test Level (Pass the Important Reliability Test-Industrial Grade)



Internal Circuit:



Package Outline (Unit: mm):





Revision	Notes
01	Initial release

Announcement

Information in this document is believed to be accurate and reliable. However, NJSME does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to Make Changes

NJSME reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

The datasheet with “REV.” + “Arabic numerals” is based on engineering data for initial reference purpose only.

The released datasheet would be issued with “REV.” + “alphabet characters”.